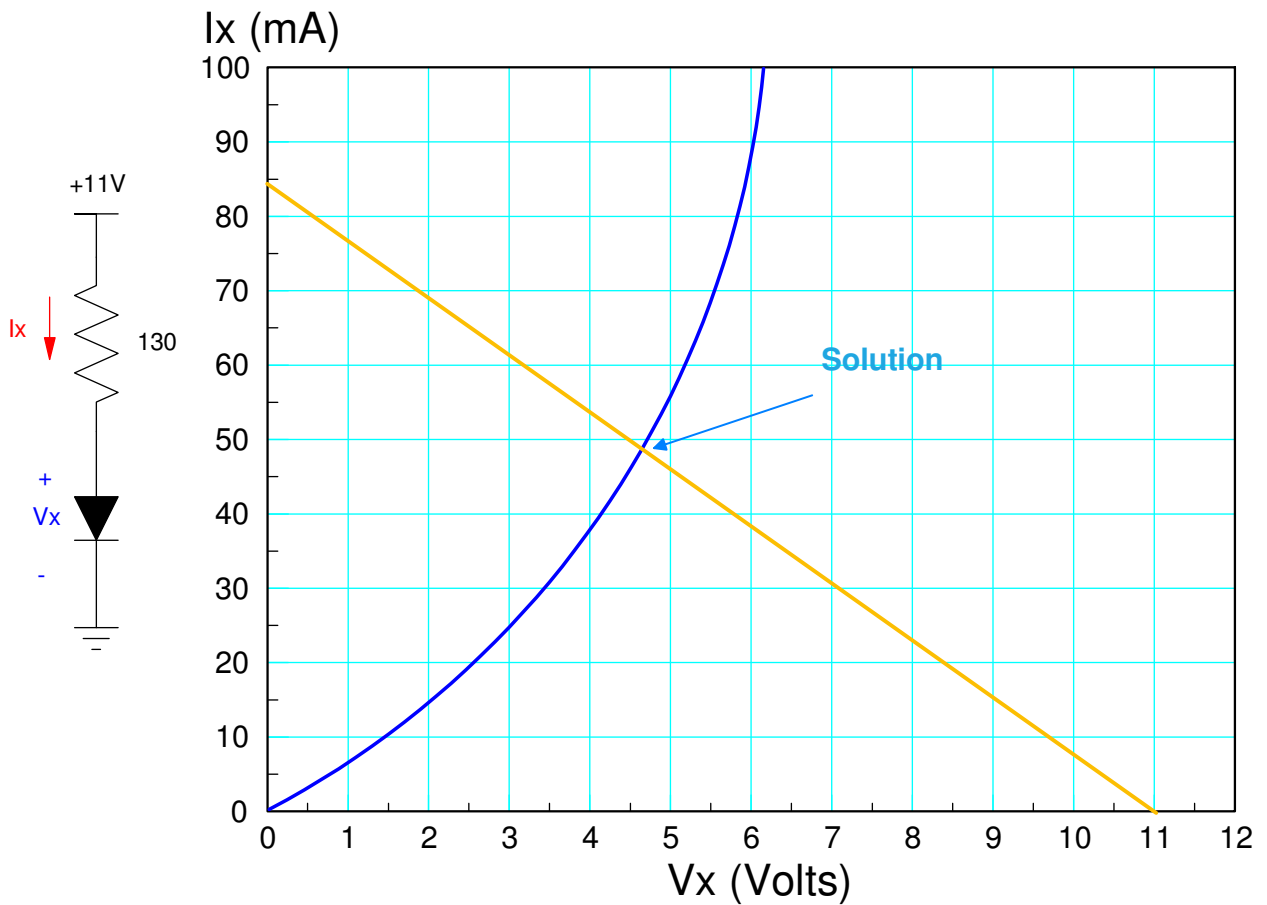


# ECE 320 - Final (pt 1) - Name \_\_\_\_\_

## Semiconductors & Diodes

1) Load Lines: Assume the VI characteristics for the diode is as shown in the graph. Draw the load line for the following circuit and determine  $I_x$  and  $V_x$ .

Load Line	$V_x$	$I_x$
show on graph	<b>4.6V</b>	<b>48mA</b>



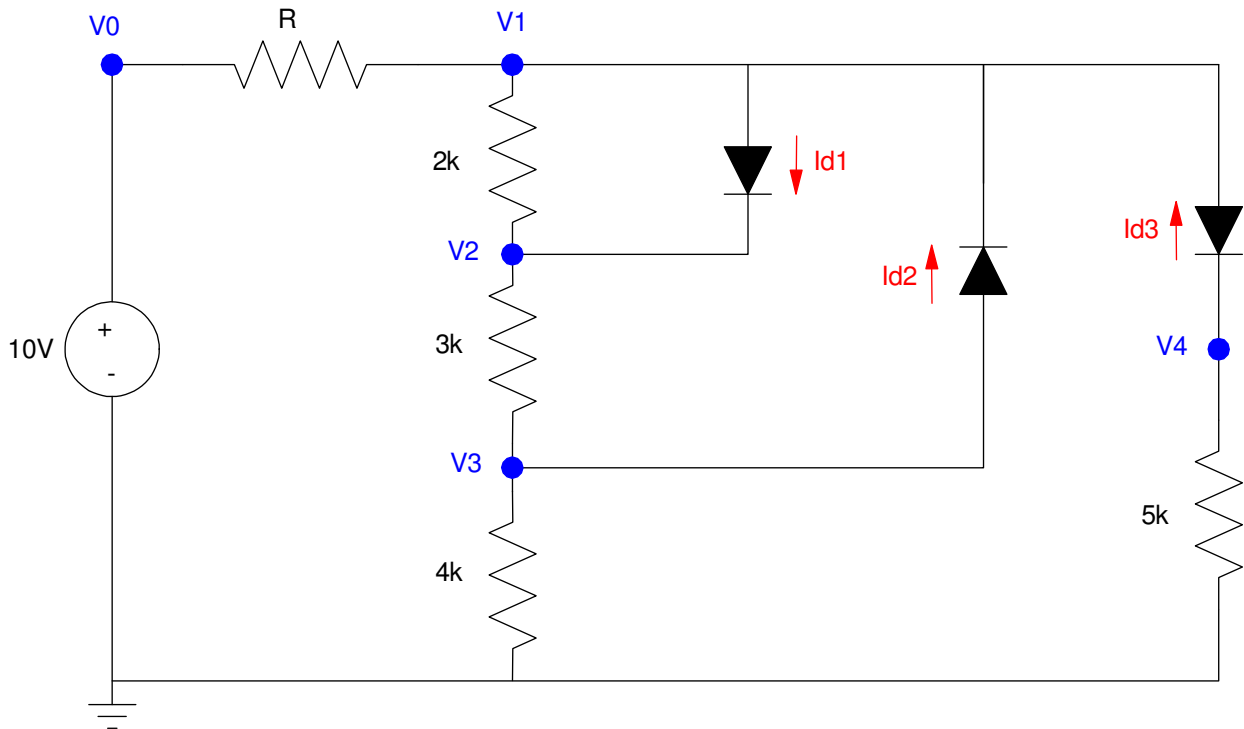
2) Nonlinear equations: Diode circuit

Assume the VI characteristics for the diodes shown below are

$$V_d = 0.052 \ln(10^8 \cdot I_d + 1) \quad I_d = 10^{-8} \cdot \left( \exp\left(\frac{V_d}{0.052}\right) - 1 \right)$$

Write N equations to solve for N unknowns: {V1, V2, V3, V4, Id1, Id2, Id3}.

- Note: you do not need to solve.
- $R = 1000 + 100 \cdot (\text{your birth month}) + (\text{birth date})$ . For example, May 14th gives 1514 Ohms.



$$I_{d1} = 10^{-8} \cdot \left( \exp\left(\frac{V_1 - V_2}{0.052}\right) - 1 \right)$$

$$I_{d2} = 10^{-8} \cdot \left( \exp\left(\frac{V_3 - V_1}{0.052}\right) - 1 \right)$$

$$-I_{d3} = 10^{-8} \cdot \left( \exp\left(\frac{V_1 - V_4}{0.052}\right) - 1 \right)$$

$$\left( \frac{V_1 - V_0}{R} \right) + \left( \frac{V_1 - V_2}{2k} \right) + I_{d1} - I_{d2} - I_{d3} = 0$$

$$\left( \frac{V_2 - V_1}{2k} \right) + \left( \frac{V_2 - V_3}{3k} \right) - I_{d1} = 0$$

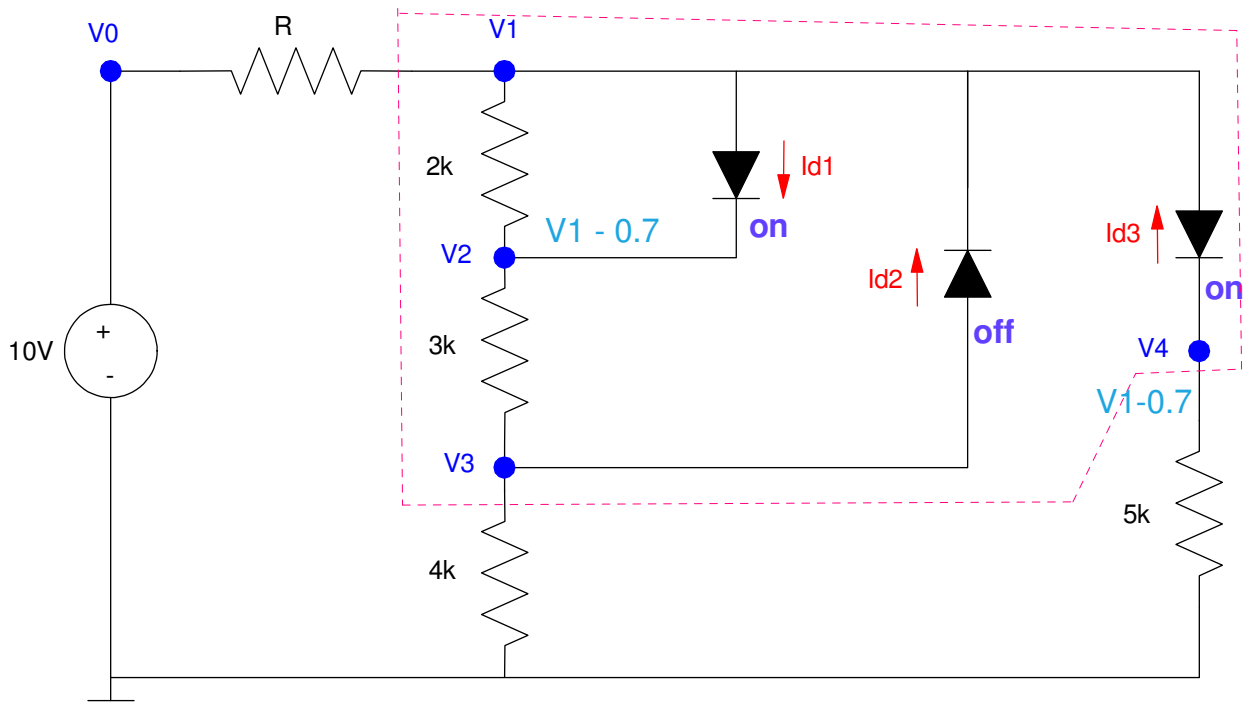
$$\left( \frac{V_3 - V_2}{3k} \right) + \left( \frac{V_3}{4k} \right) + I_{d2} = 0$$

$$I_{d3} + \left( \frac{V_4}{5k} \right) = 0$$

3) Ideal Silicon Diodes. Assume the diodes in this circuit are ideal silicon diodes:

- $V_d = 0.7V$        $I_d > 0$
- $I_d = 0$              $V_d < 0.7V$
- $R = 1000 + 100*(\text{your birth month}) + (\text{birth date})$ . For example, May 14th gives 1514 Ohms.

R 1000 + 100*mo + day	V1	V2	V3
<b>1514</b>	<b>6.8221V</b>	<b>6.1221V</b>	<b>3.4983V</b>



SuperNode

$$\left(\frac{V_1 - 10}{1514}\right) + \left(\frac{V_3}{4k}\right) + \left(\frac{V_1 - 0.7}{5k}\right) = 0$$

Node V3

$$\left(\frac{V_3 - (V_1 - 0.7)}{3k}\right) + \left(\frac{V_3}{4k}\right) = 0$$

Solving

$$V_3 = \left(\frac{4}{7}\right)(V_1 - 0.7)$$

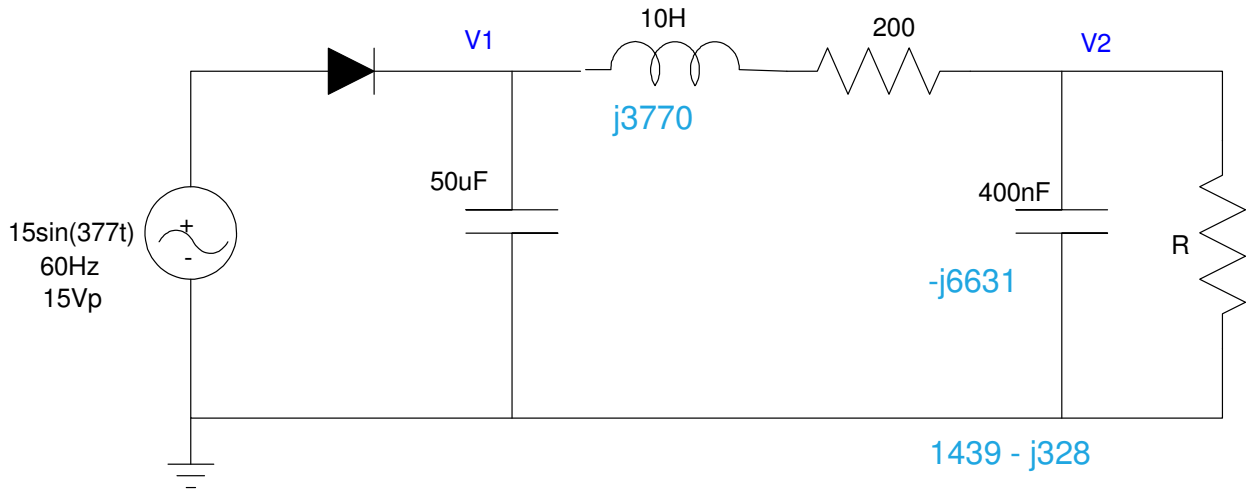
$$V_1 = 6.8221V$$

$$V_2 = V_1 - 0.7 = 6.1221V$$

$$V_3 = 3.4983V$$

4) AC to DC: Analysis: Determine V1 and V2 (both DC and AC) for the following AC to DC converter

R	V1		V2	
	DC	AC	DC	AC
<b>1514</b>	<b>12.91V</b>	<b>2.781Vpp</b>	<b>11.40V</b>	<b>1.077V<sub>pp</sub></b>



$$\max(V1) = 14.3V$$

$$I \approx \left( \frac{14.3V}{R+200} \right) = 8.34mA$$

$$I = C \cdot \frac{dV}{dt}$$

$$8.34mA = 50\mu F \cdot \frac{dV}{1/60s}$$

$$dV = 2.781V = V_{1pp}$$

$$V_1(DC) = 14.3V - \frac{1}{2} \cdot 2.781V_{pp} = 12.91V$$

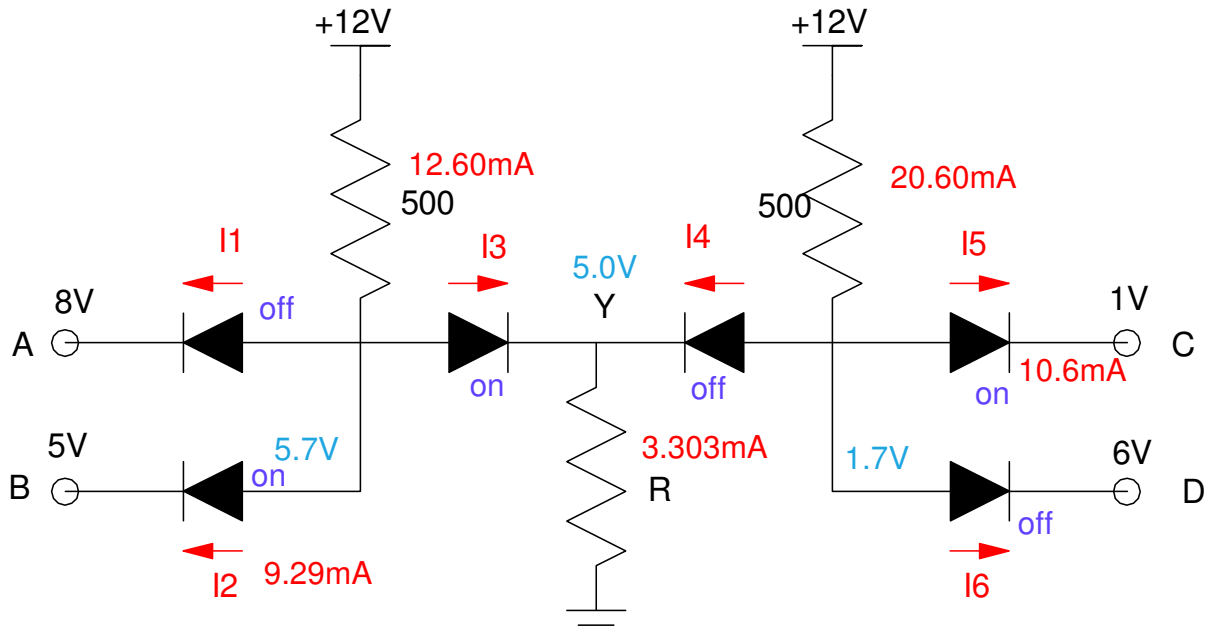
$$V_2(DC) = \left( \frac{1514}{1514+200} \right) V_1(DC) = 11.40V$$

$$V_2(AC) = \left( \frac{1439-j328}{(1439-j328)+(200+j3770)} \right) V_1(AC) = 1.077V_{pp}$$

5) Max/Min: Analysis: Determine currents I1..I6. Assume

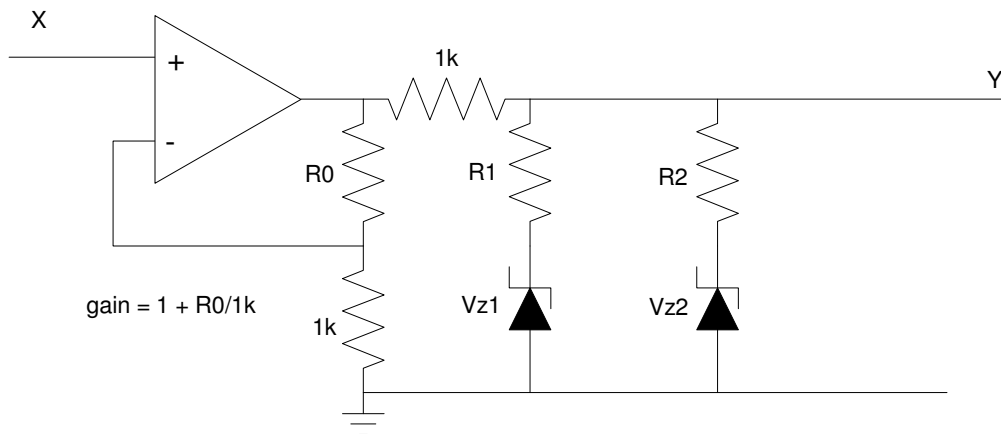
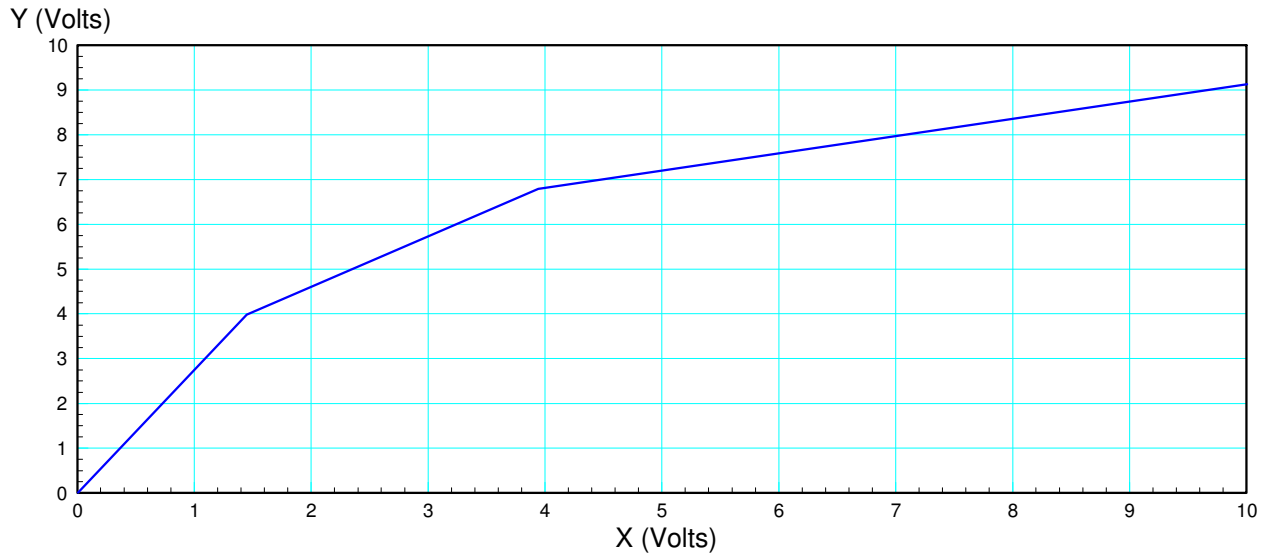
- Ideal silicon diodes ( $V_f = 0.7V$ )
- $R = 1000 + 100 * (\text{your birth month}) + (\text{birth date})$

R	I1	I2	I3	I4	I5	I6
<b>1514</b>	<b>0</b>	<b>9.29mA</b>	<b>3.303mA</b>	<b>0</b>	<b>20.6mA</b>	<b>0</b>



6) Clipper Design: Determine the resistor and zener voltages to implement the following function

R0	Vz1	R1	Vz2	R2

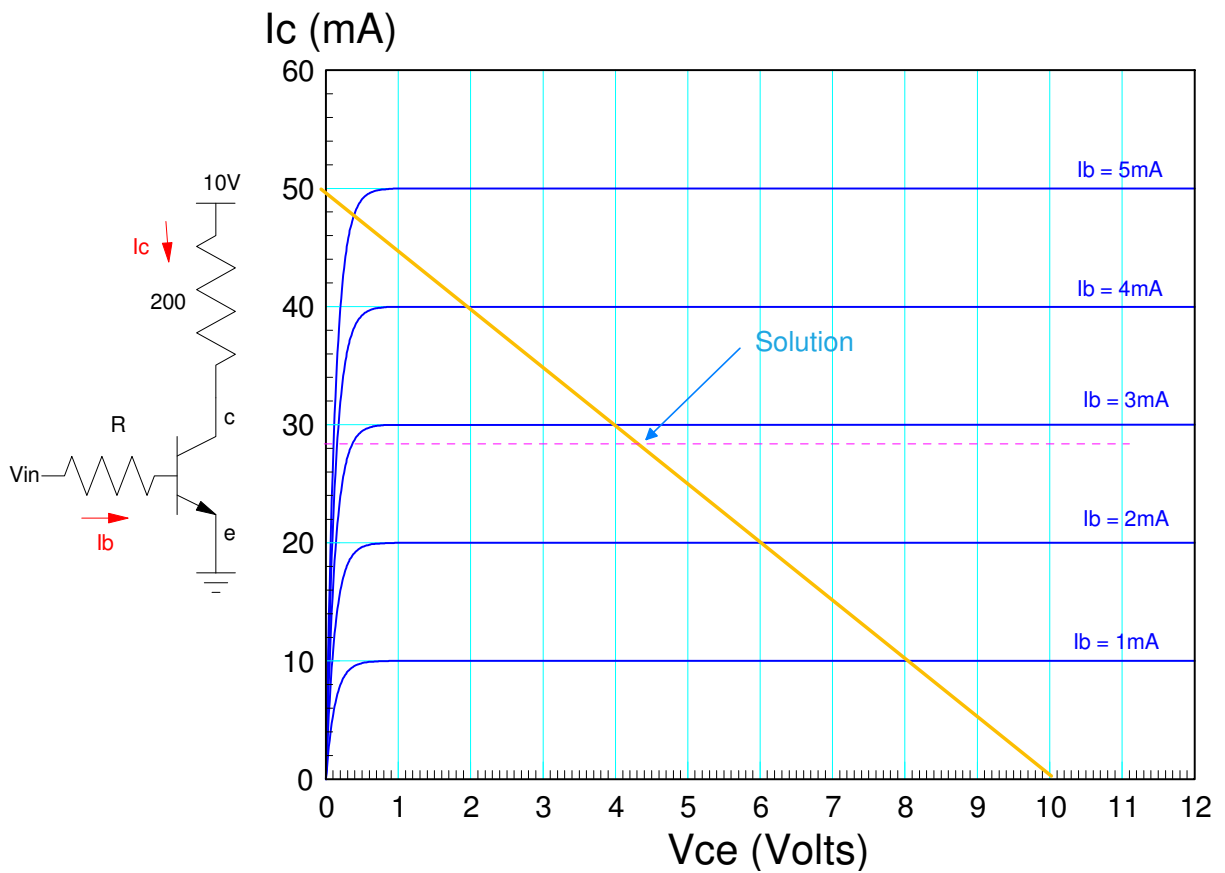


# ECE 320 - Final (pt 2) - Name \_\_\_\_\_

## Transistors and Mosfets

6) Determine the current gain,  $\beta$ . Also draw the load line and determine the operating point when  $V_{in} = 5V$

R 1000 + 100*Mo + Day	Current Gain $h_{fe} = \beta$	Load Line	Vce	Ic
<b>1514</b>	<b>10</b>	show on graph	<b>4.2V</b>	<b>28mA</b>

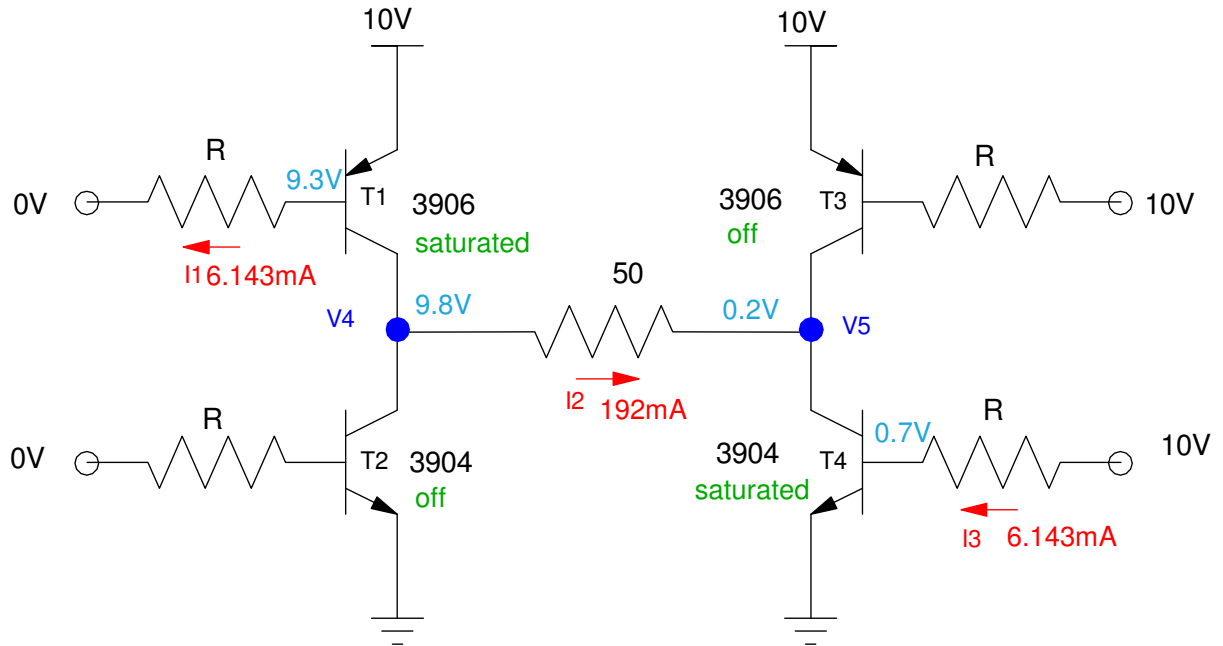


7) H-Bridge: Assume

- $R = 1000 + 100 * (\text{birth month}) + (\text{birth day})$ . May 14th would give 1514 Ohms
- Ideal silicon transistors ( $V_{be} = 0.7V$ ,  $V_{ce(sat)} = 0.2V$ ,  $\beta = 100$ )

Determine the currents for voltages for the following H bridge.

R 1000 + 100*Mo + Day	I1	I2	I3	V4	V5
<b>1514</b>	<b>6.143mA</b>	<b>192mA</b>	<b>6.143mA</b>	<b>9.8V</b>	<b>0.2V</b>



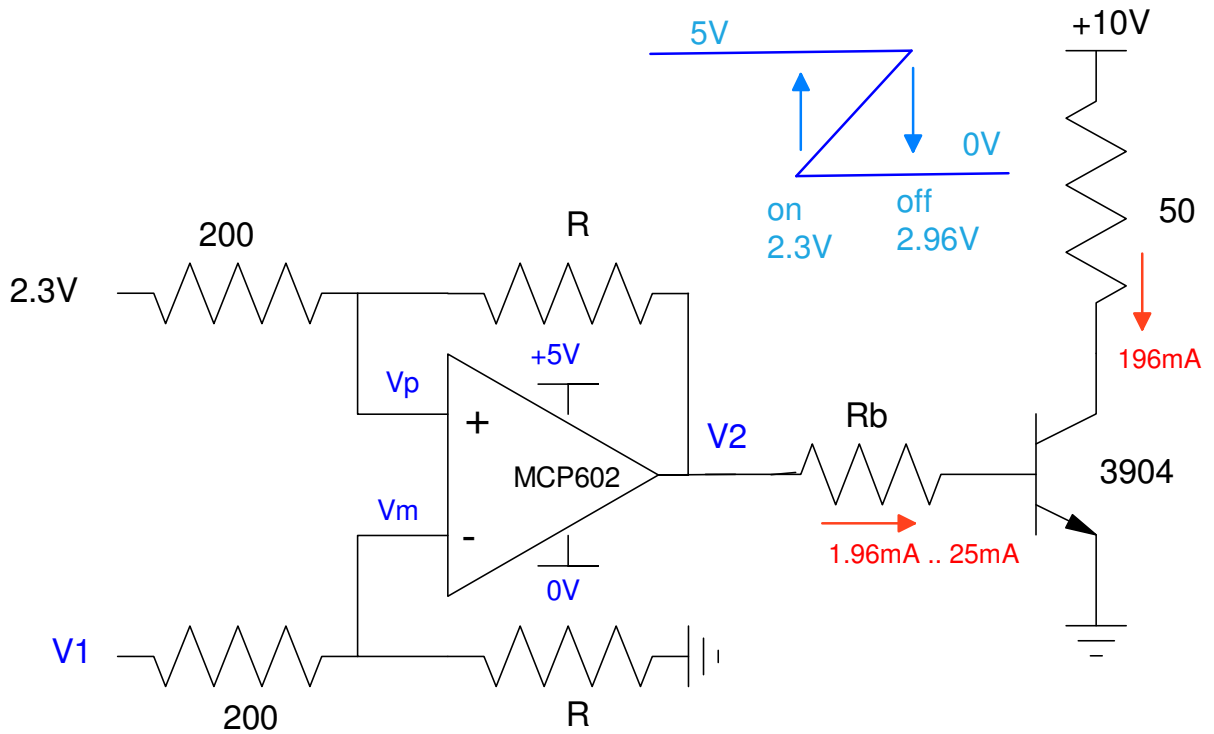


8) Schmitt Trigger: For the following Schmitt trigger, determine

- The voltage at V1 where V2 goes,
- The voltage at V1 where V2 goes low, and
- Rb so that the transistor is saturated when V2 = +5V

Let  $R = 1000 + 100 * (\text{birth month}) + (\text{birth day})$

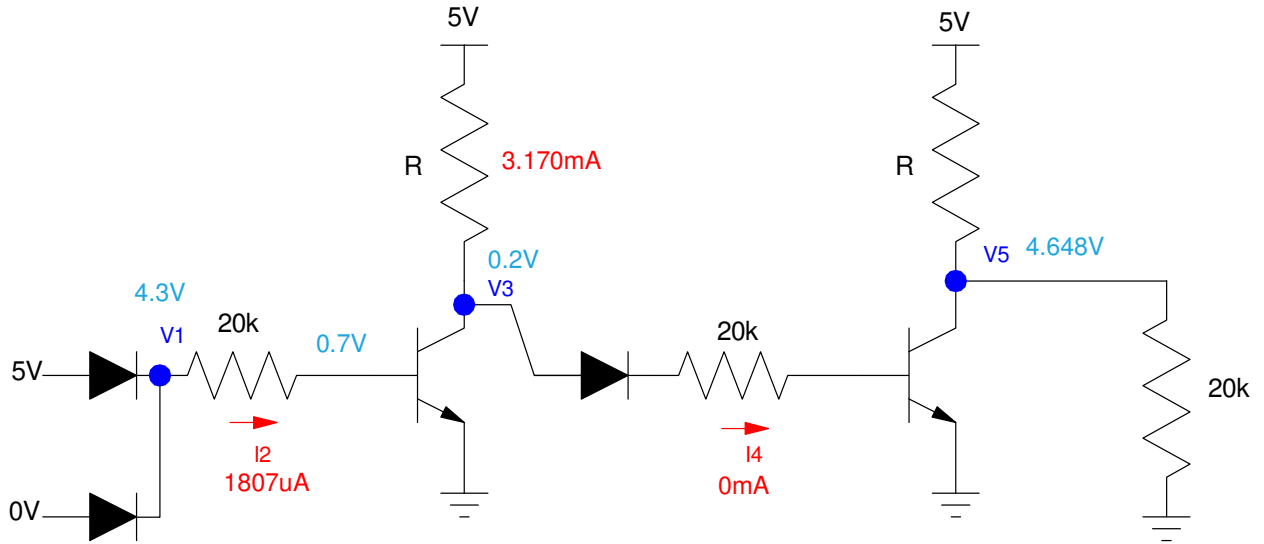
R 1000 + 100*Mo + Day	V1(on) Voltage at V1 where V2 goes high	V1(off) Voltage at V1 where V2 goes low	Rb Pick Rb so that the transistor saturates
<b>1514</b>	<b>2.3V</b>	<b>2.96V</b>	<b>172 &lt; Rb &lt; 2150</b> 25mA < Ib < 1.96mA



9) DTL Logic: Determine the voltages and currents for the following DTL logic gage. Assume

- $R = 1000 + 100 \cdot (\text{your birth month}) + (\text{birth day})$
- Ideal silicon diodes ( $V_f = 0.7V$ ), and
- Ideal 3904 transistors ( $V_{be} = 0.7V$ ,  $V_{ce(sat)} = 0.2V$ ,  $\beta = 100$ )

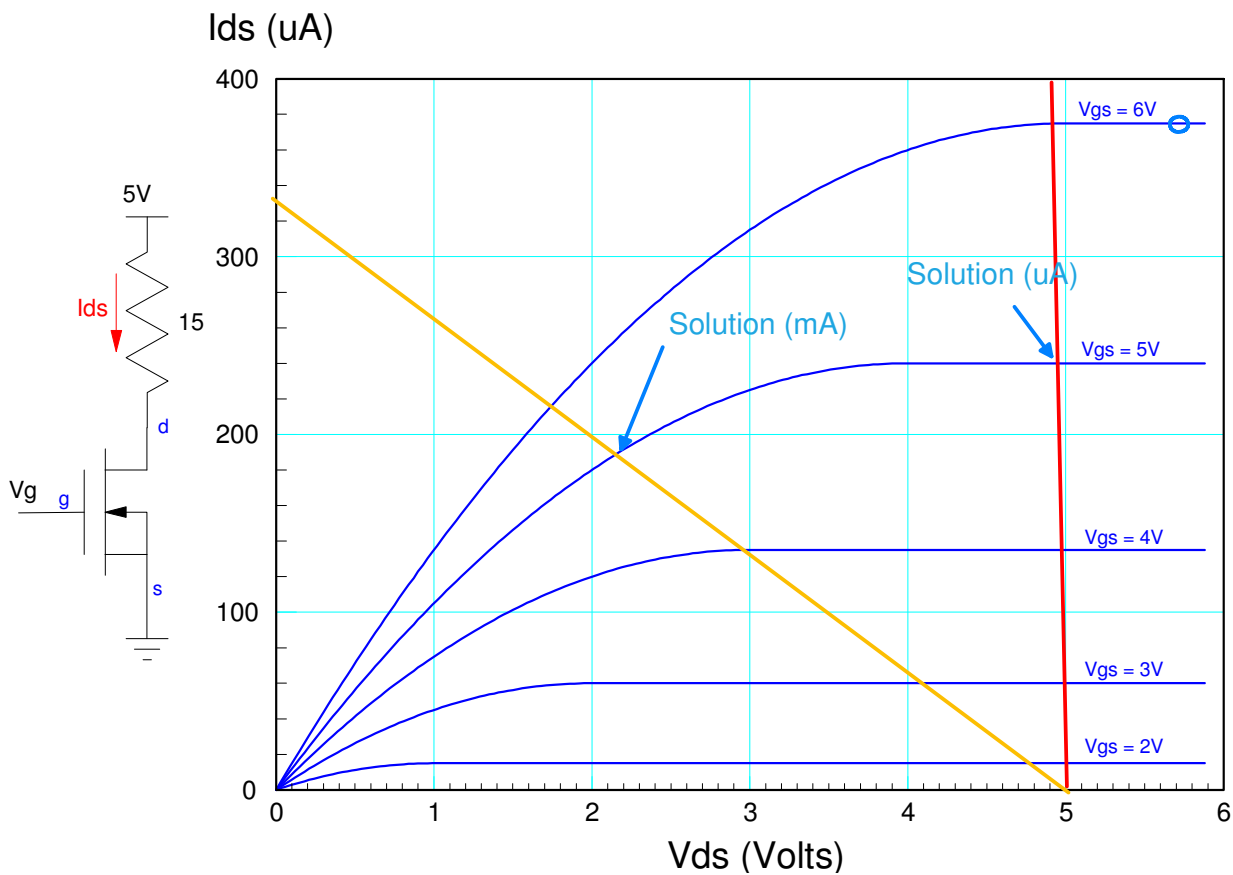
R	V1	I2	V3	I4	V5
<b>1514</b>	<b>4.3V</b>	<b>180uA</b>	<b>0.2V</b>	<b>0mA</b>	<b>4.648V</b>



10) MOSFET Load Line: For the following MOSFET circuit

- Determine the transconductance gain,  $k_n$ ,
- Draw the load line, and
- Determine  $\{V_{ds}, I_{ds}\}$  when  $V_g = 5V$

$k_n$ transconductance gain	Load Line	$I_{ds}$	$V_{ds}$	Operating Region off / active / ohmic
30.4 $\mu A/V^2$ or 30.4 $mA/V^2$	show on graph	240 $\mu A$ or 190mA	4.95V or 2.2V	saturated or ohmic



Pick a point A (saturated region)

$$I_{ds} = \frac{k_n}{2}(V_{gs} - V_{th})^2$$

$$380\mu A = \frac{k_n}{2}(6 - 1)^2$$

$$k_n = 30.4 \frac{\mu A}{V^2}$$